

# FS10ASJ-3

HIGH-SPEED SWITCHING USE

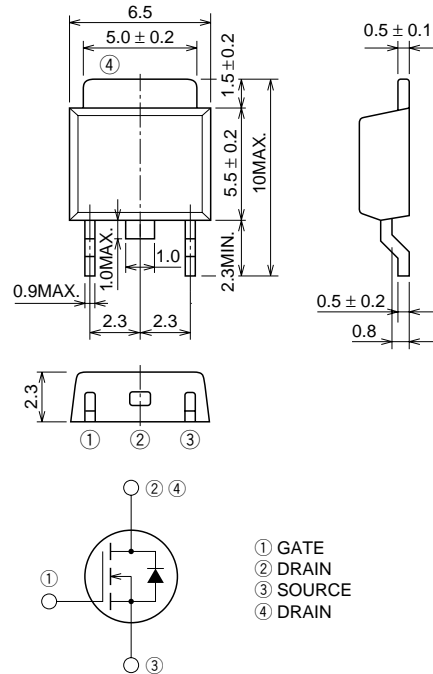
## FS10ASJ-3



- 4V DRIVE
- $V_{DSS}$  ..... 150V
- $r_{DS(ON)}$  (MAX) ..... 160m $\Omega$
- $I_D$  ..... 10A
- Integrated Fast Recovery Diode (TYP.) ..... 90ns

## OUTLINE DRAWING

Dimensions in mm



MP-3

## APPLICATION

Motor control, Lamp control, Solenoid control  
DC-DC converter, etc.

## MAXIMUM RATINGS (Tc = 25°C)

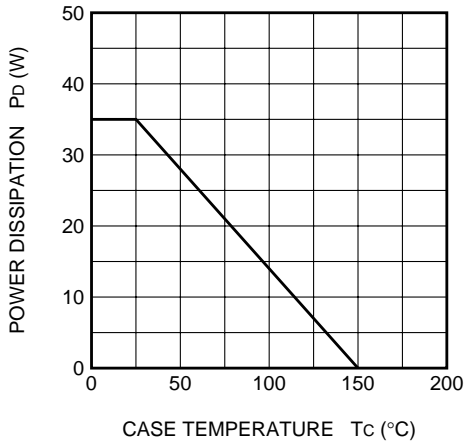
Symbol	Parameter	Conditions	Ratings	Unit
$V_{DSS}$	Drain-source voltage	$V_{GS} = 0V$	150	V
$V_{GSS}$	Gate-source voltage	$V_{DS} = 0V$	±20	V
$I_D$	Drain current		10	A
$I_{DM}$	Drain current (Pulsed)		40	A
$I_{DA}$	Avalanche drain current (Pulsed)	$L = 100\mu H$	10	A
$I_S$	Source current		10	A
$I_{SM}$	Source current (Pulsed)		40	A
$P_D$	Maximum power dissipation		35	W
$T_{ch}$	Channel temperature		-55 ~ +150	°C
$T_{stg}$	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.26	g

**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

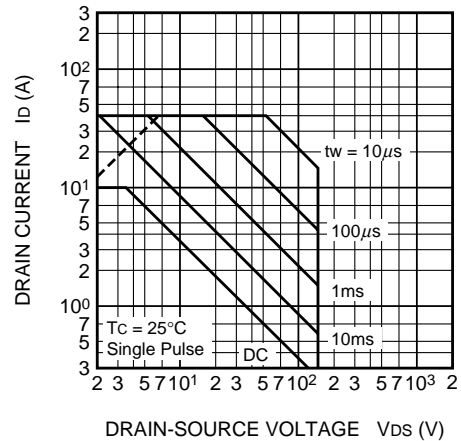
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	150	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 150V, VGS = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS (ON)	Drain-source on-state resistance	ID = 5A, VGS = 10V	—	120	160	mΩ
rDS (ON)	Drain-source on-state resistance	ID = 5A, VGS = 4V	—	125	165	mΩ
VDS (ON)	Drain-source on-state voltage	ID = 5A, VGS = 10V	—	0.60	0.80	V
yfs	Forward transfer admittance	ID = 5A, VDS = 10V	—	18	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	1800	—	pF
Coss	Output capacitance		—	180	—	pF
Crss	Reverse transfer capacitance		—	85	—	pF
td (on)	Turn-on delay time	VDD = 80V, ID = 5A, VGS = 10V, RGEN = RGS = 50Ω	—	17	—	ns
tr	Rise time		—	23	—	ns
td (off)	Turn-off delay time		—	150	—	ns
tf	Fall time		—	75	—	ns
VSD	Source-drain voltage	IS = 5A, VGS = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	3.57	°C/W
trr	Reverse recovery time	IS = 10A, dis/dt = -100A/μs	—	90	—	ns

**PERFORMANCE CURVES**

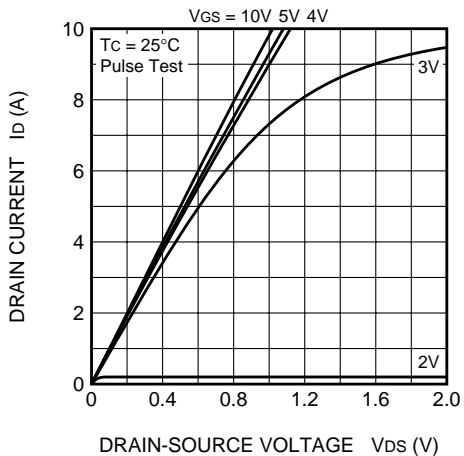
**POWER DISSIPATION DERATING CURVE**



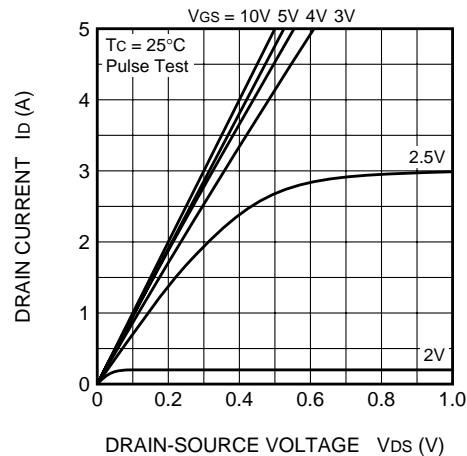
**MAXIMUM SAFE OPERATING AREA**

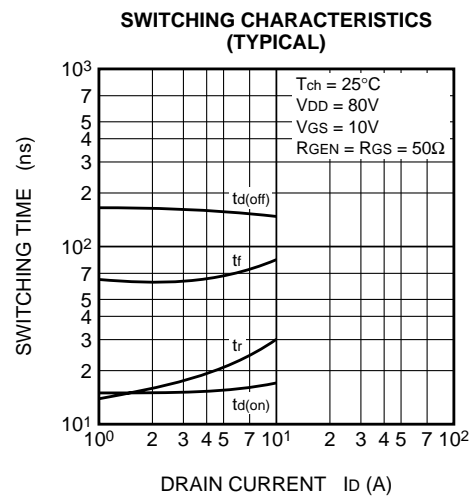
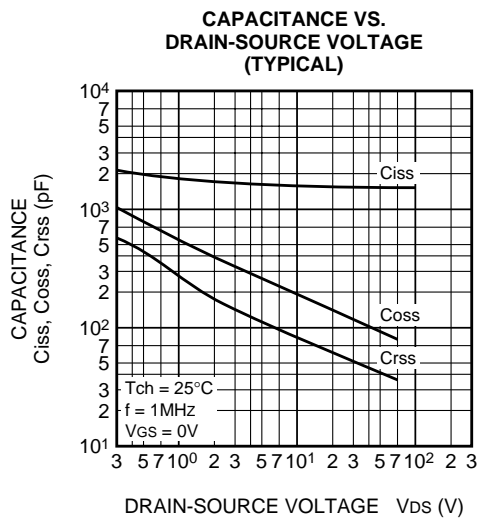
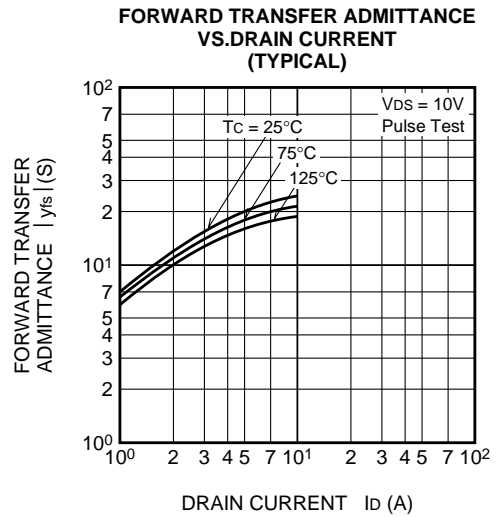
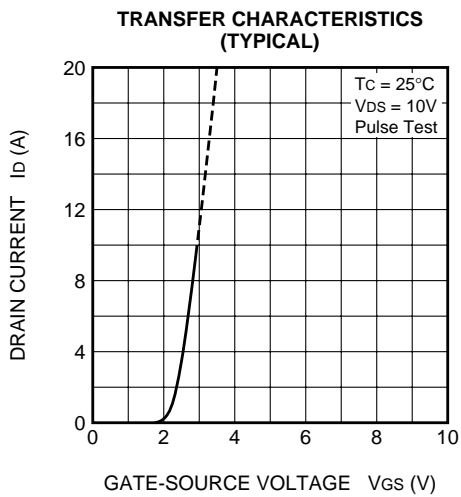
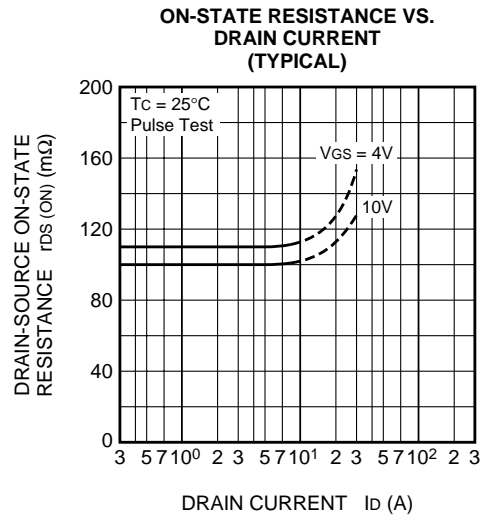
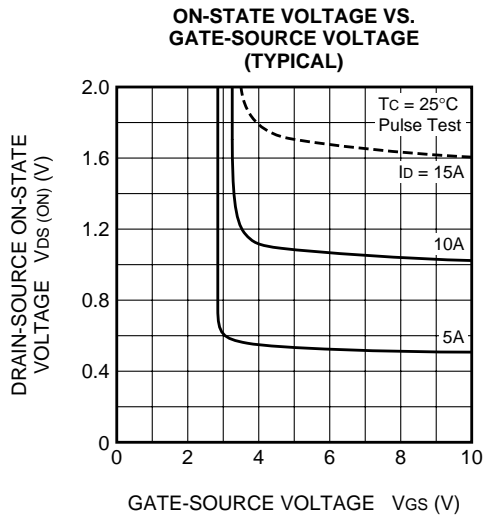


**OUTPUT CHARACTERISTICS (TYPICAL)**

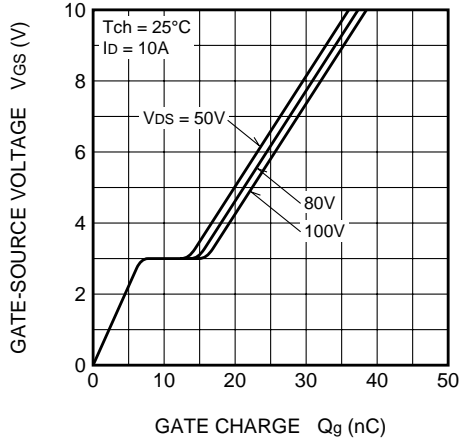


**OUTPUT CHARACTERISTICS (TYPICAL)**

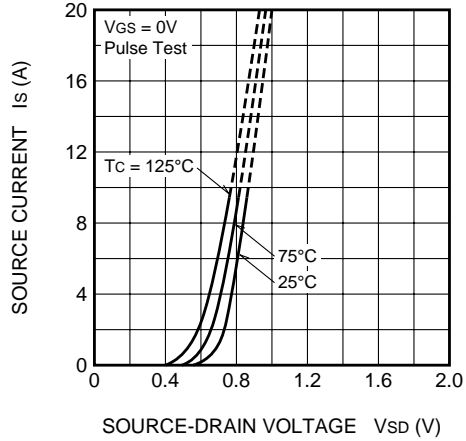




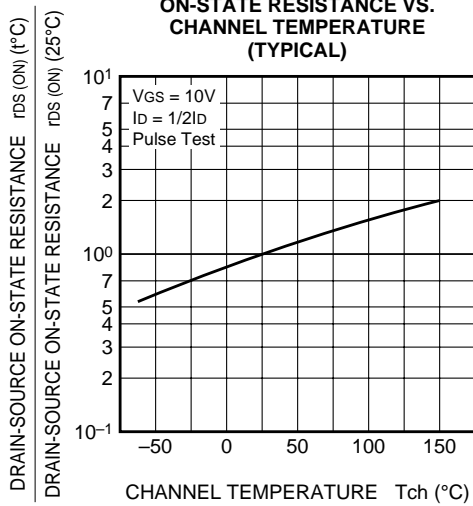
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



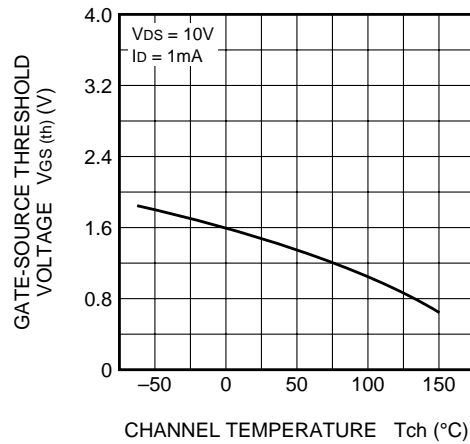
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



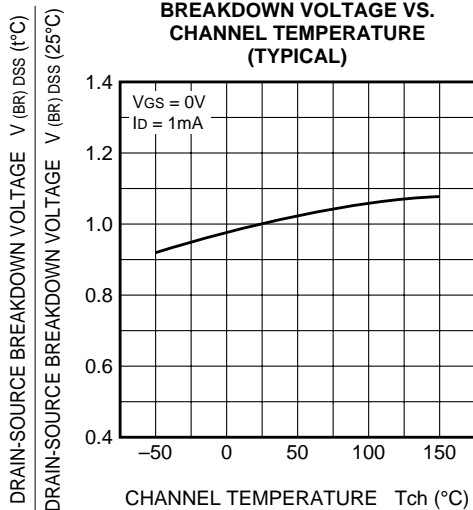
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

